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Synthesis and thermoelectric properties of *p*-type barium-filled skutterudite $Ba_vFe_xCo_{4-x}Sb_{12}$

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Single-phase barium-filled skutterudite compounds, $Ba_yFe_xCo_{4-x}Sb_{12}$ (x = 0 to 3.0, y = 0 to 0.7), were synthesized by a two-step solid-state reaction method. The maximum filling fraction of Ba (y_{max}) in $Ba_yFe_xCo_{4-x}Sb_{12}$ increased with increasing Fe content and was found to be rather greater than that of $Ce_yFe_xCo_{4-x}Sb_{12}$. The y_{max} varied from 0.35 to near 1.0 when Fe content changed from 0 to 4.0. $Ba_yFe_xCo_{4-x}Sb_{12}$ showed *p*-type conduction at a composition range of x = 0 to 3.0, y = 0 to 0.7. Carrier concentration and electrical conductivity increased with increasing Fe content and decreased with increasing Ba filling fraction. The Seebeck coefficient increased with increasing Ba filling fraction and reached a minimum at a certain Ba filling fraction (y = 0.3 to 0.4). The greatest *ZT* value of 0.9 was obtained at 750 K for *p*-type $Ba_{0.27}Fe_{0.98}Co_{3.02}Sb_{12}$. It is expected that further investigation on the optimization of filling fraction would result in a higher *ZT* value at the moderately low Fe content region.

I. INTRODUCTION

Filled skutterudite compounds have received great attention as potential thermoelectric materials recently.¹⁻⁴ It is believed that the filling of the Sb-icosahedron voids by rare-earth and other metallic atoms significantly depresses the lattice thermal conductivity due to the rattling of these atoms positioned in the oversized voids.^{1-3,5-8} Moreover, the filling fraction of rare-earth atoms also remarkably influences carrier properties (carrier type, concentration, mobility, and effective mass) and electrical transport properties of filled skutterudite compounds. However, filling fraction is dependent on oxidation valence of filling atoms and Fe/Co ratio and is difficult to change as desirable. For example, in the $Ln_vFe_xCo_{4-x}Sb_{12}$ (Ln = Ce, La) structure, Ce and La are generally thought of as trivalent; i.e., one Ce or La provides three electrons to the skutterudite structure.^{4–6,9–15} Replacing Co with Fe in CoSb₃ leads to the creation of one hole in the valence band.^{1,4,16,17} The crystallographicstability and charge balance requires a match between the

filling fraction and the Fe/Co intersubstitution for charge compensation. Therefore, rare-earth ions such as Ce^{3+} and La^{3+} have only a small filling fraction because of their high oxidation valence. Furthermore, it has been found that the amount of rare-earth atoms that can be incorporated into the structure decreases significantly when Co content increases.^{4,10–12} The low solubility of rare-earth atoms has become an obstacle for adjusting carrier concentration and optimizing thermoelectric properties in the Co-rich composition.

On the other hand, it is known that CoSb_3 skutterudite decomposes at 1147 K by a peritectic reaction¹⁸ and that the peritectic temperature decreases dramatically as Co is replaced by Fe.⁹ For thermoelectric application, it is desirable to use thermoelectric materials that are characterized by not only high thermoelectric performance but also by good high-temperature stability. Consequently, it is necessary to find filled skutterudites on the Co-rich composition side with a high filing fraction.

From the viewpoint of crystal chemistry, it is expected

that a higher filling fraction in the Co-rich composition side would be obtained if divalent atoms, such as alkaline-earth atoms, were to fill in the Sb-icosahedron voids in the skutterudite structure. The advantage would be the ability to control and adjust carrier concentration, and further optimize and improve thermoelectric properties of filled skutterudite compounds in a wide composition range. So far, Stetson et al.¹⁶ synthesized BaFe₄Sb₁₂ and BaRu₄Sb₁₂ filled by Ba²⁺, but no report was found on the synthesis and the thermoelectric properties of $Ba_v Fe_x Co_{4-x} Sb_{12}$. In the present study, p-type barium-filled skutterudite compounds $Ba_{y}Fe_{x}Co_{4-x}Sb_{12}$ (x = 0 to 3.0, y = 0 to 0.7), were synthesized by a two-step solid-state reaction method. The effects of Ba filling fraction and Fe content on thermoelectric properties were investigated. The effects of the oxidation valence of filling atoms on electrical transport properties of $M_v Fe_x Co_{4-x} Sb_{12}$ (M = Ba, Ce) are discussed.

II. EXPERIMENTAL

Highly pure metals of Ba (99.9%, plate), Sb (99.9999%, powder), Fe (99.99%, powder) and Co (99.99%, powder) were used as starting materials. Because the reaction between Ba and Sb or Co(Fe) is highly exothermic, it is difficult to directly melt or react a mixture of the constituent elements. In the present study, a two-step solid reaction was used. A binary compound of Ba₃Sb and a ternary compound of $Fe_{r}Co_{1-r}Sb_{2}$ were first synthesized by reacting the constituent elements in a flowing Ar atmosphere. Reaction temperature and reaction time were 903 K, 96 h and 973 K, 168 h for the synthesis of Ba₃Sb and $Fe_xCo_{1-x}Sb_2$, respectively. For the synthesis of a Ba₃Sb compound, it is important that the samples are heated slowly (<1 K/min) from room temperature to 793 K and kept at that point for 12 h before being heated to the reaction temperature (903 K). The resulting compounds, Ba₃Sb and Fe_xCo_{1-x}Sb₂, were then crushed and mixed with Sb in various Ba:(Fe + Co):Sb = y:4:12molar ratios and pressed into pellets. The pellets were heated at 973 K under an Ar atmosphere for 96 h. The reacted materials were milled into fine powder and washed with HCl + HNO3 to remove a slight amount of impurity phases (Sb and $Fe_rCo_{1-r}Sb_2$). To form a fully dense polycrystalline solid, the obtained powder was sintered by the plasma activated sintering (PAS) method. Sintering was performed at a temperature of 873 K for 15 min. Samples of $3 \times 4 \times 15 \text{ mm}^3$, $\phi 10 \times 1.5 \text{ mm}^3$, and $5 \times 5 \times 0.3 \text{ mm}^3$ in size were cut from the sintered material for measurements of electrical conductivity/ Seebeck coefficient, thermal conductivity, and Hall coefficient, respectively.

The constituent phases of the samples were determined by powder x-ray diffractometry (Rigaku, RAD-C, Cu K_{α} , Tokyo, Japan). The chemical compositions of the samples were analyzed by inductively coupled plasma emission spectroscopy (ICPES). The crystal structure of $Ba_{v}Fe_{x}Co_{4-x}Sb_{12}$ were refined by Rietveld analysis using the x-ray powder diffraction data in a wide 2θ range (10 to 130°). The Hall coefficient ($R_{\rm H}$) was measured using the van der Pauw method with an excitation current of 100 mA and a magnetic field of 5028 Gauss. The carrier concentration (p) was calculated from the Hall coefficient ($R_{\rm H}$), using $p = 1/R_{\rm H}e$ where e is the electron charge. The electrical conductivity $(\boldsymbol{\sigma})$ was measured by the standard four-probe method in a flowing Ar atmosphere. The thermoelectromotive force (ΔE) was measured under temperature differences (ΔT) of 0 to 10 K, and the Seebeck coefficient (α) was obtained from the slope of ΔE versus ΔT plot. The thermal conductivity (κ) was measured by a laser flash method (Shinkuriko, TC-7000, Yokohama, Japan) in a vacuum. All the measurements were performed in a temperature range of 300 to 800 K. The dimensionless figure of merit $(ZT = \alpha^2 \sigma T/\kappa)$ was calculated using measured electrical conductivity, Seebeck coefficient, and thermal conductivity.

III. RESULTS AND DISCUSSION

A. Synthesis and structure

When Ba and Sb were pre-reacted at 903 K for 96 h, Sb₃Ba was obtained with a slight amount of remaining Sb. When Fe + Co + Sb were pre-reacted at 973 K for 168 h, Fe_xCo_{1-x}Sb₂ was synthesized. After the second-step reaction at 973 K, the single phase of Ba_yFe_xCo_{4-x}Sb₁₂ was obtained when $x \le 2$, but the reacted powder consisted of Ba_yFe_xCo_{4-x}Sb₁₂ as the main phase with a trace impurity phase of Sb and Fe_xCo_{1-x}Sb₂ when x > 2. The impurity phases (Sb and Fe_xCo_{1-x}Sb₂) were removed with a HCl + HNO₃ mixed acid.

Rietveld analysis was used to determine and refine the crystal structure of the synthesized $Ba_yFe_xCo_{4-x}Sb_{12}$.¹⁹ The resulting unit cell was consistent with filled skutterudite having space group of *Im3*. The refined Ba filling fraction (y) was in good agreement with the Ba contents by ICPES analysis. Atomic coordinates for the Sb site differed slightly from those of CoSb₃ but were close to those of $BaFe_4Sb_{12}$.¹⁶ The thermal parameters (*B*) of Ba, Sb, and Co/Fe were 0.61, 0.16, and 0.12, respectively. Sales *et al.*² and Chakoumakos *et al.*⁶ have reported that the thermal parameter values (the atomic displacement parameters) can be used to determine the degree of the vibration of the atom about its equilibrium position. They also indicated that the anomalously large value of the thermal parameter of the La atom in Ln_yFe_xCo_{4-x}Sb₁₂ means that the La is poorly bound

in the structure and rattles about its equilibrium position. In the present study, the finding of $B_{Ba} \gg B_{Sb}$ and $B_{Ba} \gg B_{Fe/Co}$ supported the possibility that Ba atoms rattled in Ba_yFe_xCo_{4-x}Sb₁₂. B_{Ba} was smaller than that of Ce or La in Ln_yFe_xCo_{4-x}Sb₁₂. This may be due to the large ionic radius of Ba,¹⁹ implying that the ionic size of the filling atoms gives influence on the thermal parameters.

The relationship between the maximum filling fraction (y_{max}) of Ba and Fe content (x) is shown in Fig. 1, similar to that observed in the $Ce_yFe_xCo_{4-x}Sb_{12}$ system. ^{11,12,20,21} The y_{max} of Ba increased with Fe content, and it was larger than that of Ce. For example, at x = 0 and 1.0, y_{max} of Ba in $Ba_v Fe_x Co_{4-x} Sb_{12}$ was about 0.35 and 0.5 in the present experiment, while that of Ce in $Ce_{v}Fe_{x}Co_{4-x}Sb_{12}$ has been reported to be about 0.067 and 0.31. The difference between y_{max} (Ba) and y_{max} (Ce) may be caused by the difference in valence between Ba (2+) and Ce (3+). However, it is notable that the filling fraction did not change simply in proportion to the difference of valence. In other words, at lower Fe contents, the difference of filling fraction between Ba and Ce was much larger than that at higher Fe content. As Fe content increased, the difference between y_{max} (Ba) and y_{max} (Ce) decreased. At x = 4.0, the filling limits of both Ba and Ce reached nearly 1.0. The reason for the nonlinear relation between the valence and filling fraction is unknown, and further investigation of the crystal structure and valence band is required. In addition, when Ba is used as filling atom and Fe content is the same, the range of filling fraction for p- and n-type filled skutterudite compounds is larger than that of Ce used as filling



FIG. 1. Relationship between maximum Ba filling fraction and Fe content for $Ba_yFe_xCo_{4-x}Sb_{12}$. Results are compared to those obtained for $Ce_yFe_xCo_{4-x}Sb_{12}$.^{11,12}

atom. This implies that thermoelectric properties of $Ba_yFe_xCo_{4-x}Sb_{12}$ can be adjusted and optimized in a wide composition range when Ba is the filling atom.

B. Electrical properties

Table I summarizes the chemical composition, Hall coefficient and carrier concentration of $Ba_yFe_xCo_{4-x}Sb_{12}$ (x = 0 to 3.0, y = 0 to 0.7). The Hall coefficients of all samples were plus values; therefore the $Ba_yFe_xCo_{4-x}Sb_{12}$ samples show *p*-type conduction.

Figure 2 shows the effects of Ba filling fraction and Fe content on the room-temperature carrier concentration of *p*-type $Ba_vFe_xCo_{4-x}Sb_{12}$. Results are compared to those of p-type Ce_yFe_{1.5}Co_{2.5}Sb₁₂.^{12,21} Carrier concentration of p-type $Ba_vFe_xCo_{4-x}Sb_{12}$ decreased with increasing Ba filling fraction. In general, Ba is thought to be divalent in $Ba_vFe_xCo_{4-x}Sb_{12}$, i.e., one Ba^{2+} provides two electrons to the skutterudite structure. With increasing Ba filling fraction, Ba provided more of the electron to skutterudite structure and therefore resulted in a decrease of hole concentration. Further, it is possible that conduction type may change from *p*-type to *n*-type if the Ba filling fraction exceeds y_{max} . At the same Ba filling fraction, carrier concentration of $Ba_v Fe_x Co_{4-x} Sb_{12}$ increased with increasing Fe content. At y = 0.38, when Fe content increased from 1.0 to 1.6, carrier concentration increased from $9.2 \times 10^{25} \text{ m}^{-3}$ to $2.76 \times 10^{26} \text{ m}^{-3}$. It indicated that Fe mainly showed 2+ in the skutterudite structure, thus it provided less electrons to the structure than Co^{+3} . At the same Fe content and filling fraction, carrier concentration of *p*-type Ba_vFe_{1.6}Co_{2.4}Sb₁₂ was larger than that of *p*-type $\operatorname{Ce}_{v}\operatorname{Fe}_{1,5}\operatorname{Co}_{2,5}\operatorname{Sb}_{12}$. For example, when x is about 1.5, and y = 0.26, the carrier concentration of $Ba_{0.26}Fe_{1.6}Co_{2.4}Sb_{12}$ is $3.05 \times 10^{26} \text{ m}^{-3}$, while that of $Ce_{0.26}Fe_{1.5}Co_{2.5}Sb_{12}$ is 2.67 × 10²⁶ m⁻³. This is because the electron number the Ba²⁺ provided to the skutterudite structure was less than that provided by Ce^{3+} .

TABLE I. Nominal composition, composition, and some roomtemperature properties for *p*-type $Ba_yFe_xCo_{4-x}Sb_{12}$.

Sample number and nominal composition	Composition	Hall coefficient (cm ³ C ⁻¹)	Hole concentration (m ⁻³)
1. x: 1.6: y: 0.1 2. x: 1.6: y: 0.2 3. x: 1.6: y: 0.3 4. x: 1.6: y: 0.4 5. x: 1.6: y: 0.5 6. x: 1.0: y: 0.1	$\begin{array}{l} Ba_{0.13}Fe_{1.57}Co_{2.43}Sb_{12}\\ Ba_{0.26}Fe_{1.56}Co_{2.44}Sb_{12}\\ Ba_{0.38}Fe_{1.57}Co_{2.43}Sb_{12}\\ Ba_{0.38}Fe_{1.57}Co_{2.43}Sb_{12}\\ Ba_{0.54}Fe_{1.57}Co_{2.43}Sb_{12}\\ Ba_{0.63}Fe_{1.60}Co_{2.40}Sb_{12}\\ Ba_{0.10}Fe_{0.93}Co_{3.07}Sb_{12}\\ \end{array}$	$\begin{array}{c} 1.86 \times 10^{-2} \\ 1.91 \times 10^{-2} \\ 2.26 \times 10^{-2} \\ 3.28 \times 10^{-2} \\ 1.28 \times 10^{-1} \\ 3.08 \times 10^{-2} \end{array}$	$\begin{array}{c} 3.36 \times 10^{26} \\ 3.05 \times 10^{26} \\ 2.76 \times 10^{26} \\ 1.90 \times 10^{26} \\ 4.88 \times 10^{25} \\ 2.02 \times 10^{26} \end{array}$
7. x: 1.0: y: 0.2 8. x: 1.0: y: 0.3 9. x: 1.0: y: 0.4 10. x: 1.0: y: 0.5 11. x: 1.0: y: 0.6	$\begin{array}{l} Ba_{0,19}Fe_{0,92}Co_{3,08}Sb_{12}\\ Ba_{0,27}Fe_{0,98}Co_{3,02}Sb_{12}\\ Ba_{0,38}Fe_{1,01}Co_{2,99}Sb_{12}\\ Ba_{0,41}Fe_{0,98}Co_{3,02}Sb_{12}\\ Ba_{0,46}Fe_{0,98}Co_{3,02}Sb_{12}\\ \end{array}$	$\begin{array}{c} 3.17 \times 10^{-2} \\ 3.65 \times 10^{-2} \\ 6.79 \times 10^{-2} \\ 1.03 \times 10^{-1} \\ 2.13 \times 10^{-1} \end{array}$	$\begin{array}{c} 1.97 \times 10^{26} \\ 1.72 \times 10^{26} \\ 9.20 \times 10^{26} \\ 6.07 \times 10^{26} \\ 2.95 \times 10^{26} \end{array}$

These results indicate that the oxidation valence of the filling atoms influenced carrier concentration of *p*-type $M_yFe_xCo_{4-x}Sb_{12}$ (M = Ba, Ce) significantly, and larger carrier concentration would be obtained when an atom having a lower oxidation valence was used as filling atom.

The effects of Ba filling fraction on the electrical conductivity (σ) of *p*-type Ba_yFeCo₃Sb₁₂ is shown in Fig. 3. Results are compared to those of FeCo₃Sb₁₂²⁰ and



FIG. 2. Effect of Ba filling fraction and Fe content on the roomtemperature carrier concentration for *p*-type $Ba_yFe_xCo_{4-x}Sb_{12}$. Results are compared to those obtained for *p*-type $Ce_yFe_{1.5}Co_{2.5}Sb_{12}$.^{12,21}



FIG. 3. Temperature dependence of electrical conductivity for *p*-type $Ba_yFeCo_3Sb_{12}$. Results are compared to those obtained for $FeCo_3Sb_{12}$ and $Ce_{0.35}FeCo_3Sb_{12}$.^{11,20}

 $Ce_{0.35}FeCo_3Sb_{12}$.¹¹ The σ values of $Ba_yFeCo_3Sb_{12}$ decreased with increasing Ba filling fraction. This is consistent with the changes of carrier concentration shown in Fig. 2. At the maximum Ba filling fraction of 0.46, the positive temperature dependence at high temperatures was observed, implying the possibility of intrinsic behavior at high temperatures. From the slope of the $\ln\sigma$ -1/T plot at high temperatures, a band gap (E_{o}) value of 0.29 eV was calculated using $\sigma = A \exp(-E_o/kT)$ (where, σ is electrical conductivity, E_{g} is band gap, k is Boltzmann constant, T is absolute temperature, and A is a constant), which is close to the band gap value (0.4 eV \pm 0.1) reported previously for $\text{Ce}_{v}\text{Fe}_{x}\text{Co}_{4-x}\text{Sb}_{12}$.² While Fe content was the same, σ of FeCo₃Sb₁₂ was larger than that of $Ba_{0.38}FeCo_3Sb_{12}$ and $Ce_{0.35}FeCo_3Sb_{12}$. While filling fraction was the same, σ of Ba_{0.38}FeCo₃Sb₁₂ was larger than that of Ce_{0.35}FeCo₃Sb₁₂. This is consistent with the effect of oxidation valence of filling atoms on carrier concentration.

Figure 4 shows the relationship between carrier concentration and electrical conductivity for *p*-type $Ba_yFe_xCo_{4-x}Sb_{12}$ at 300 K. Results are compared to those obtained for *p*-type $Ce_yFe_xCo_{4-x}Sb_{12}$.^{12,21} Electrical conductivity increased with carrier concentration increasing for *p*-type $Ba_yFe_xCo_{4-x}Sb_{12}$ and $Ce_yFe_xCo_{4-x}Sb_{12}$. At the same carrier concentration, however, electrical conductivity of *p*-type $Ba_yFe_xCo_{4-x}Sb_{12}$ was larger than that of *p*-type $Ce_yFe_xCo_{4-x}Sb_{12}$. The reasons for the difference of electrical conductivity are not revealed. Calculations on LaT_4P_{12} indicate that both the interstitial cation and the Pn framework are important in determining the properties.¹⁶ It was also reported by Jung *et al.* that the Sb₄-ring markedly influenced electrical transport



FIG. 4. Relationship between carrier concentration and electrical conductivity for *p*-type $Ba_yFe_xCo_{4-x}Sb_{12}$ at 300 K. Results are compared to those obtained for *p*-type $Ce_yFe_xCo_{4-x}Sb_{12}$.^{12,21}

properties of the skutterudite compound (CoSb₃) and filled skutterudite (LnFe_xCo_{4-x}Sb₁₂).¹³ In CoSb₃ and LnFe_xCo_{4-x}Sb₁₂ structure, the Sb₄-ring was rectangular (for example, in the LaFe_xCo_{4-x}Sb₁₂ structure, Sb– Sb distances of the Sb₄-ring were 2.932 and 2.982 Å, respectively). But in the BaFe₄Sb₁₂ structure, the Sb₄ring was nearly square (Sb–Sb distances of Sb₄-ring are 2.952 and 2.959 Å, respectively).¹⁵ The difference of electrical transport properties for Ba_yFe_xCo_{4-x}Sb₁₂ and Ce_yFe_xCo_{4-x}Sb₁₂ may be related to different effects of Ba and Ce on the Sb–Sb distances of the Sb₄-ring in MFe_xCo_{4-x}Sb₁₂ structure.

Figure 5 shows temperature dependence of the Seebeck coefficient (α) for *p*-type Ba_yFe_{1.6}Co_{2.4}Sb₁₂. The α values increased with increasing temperature and reached a maximum at a certain temperature, T_{opt} . The T_{opt} shifted to the high temperature side as the Ba filling fraction decreased. In general, α values increase with decreasing carrier concentration and increase with increasing carrier effective mass (m^*). It was shown that the carrier effective mass of Ba_yCo₄Sb₁₂ increases with filling of Ba.²² In the present study, the increase in α of Ba-filled Ba_yFe_xCo_{4-x}Sb₁₂ may have been caused by the decrease of carrier concentration and the increase of carrier effective mass (m^*).

C. Thermal conductivity

The Wiedemann–Franz law ($\kappa_{\rm C} = L\sigma T$) using a Lorenz number of $2 \times 10^{-8} \text{ V}^2/\text{K}^2$ was used to estimate the carrier concentration contribution to the thermal conductivity.² The lattice thermal conductivity ($\kappa_{\rm L}$) was obtained by subtracting the carrier component ($\kappa_{\rm C}$) from the

total thermal conductivity. Figure 6 shows temperature dependence of lattice thermal conductivity for *p*-type Ba_yFeCo₃Sb₁₂. As shown in Fig. 6, κ_L decreased with increasing temperature. The κ_L was decreased greatly by the Ba filling in the Sb-icosahedron. The ionic radius of Ba (Ba²⁺ = 1.34 Å) is smaller than the radius of the Sb-icosahedron void (1.892 Å); thus Ba poorly bonded in the structure and can rattle about its equilibrium position. Indeed, such rattling was also confirmed by results obtained using Rietveld analysis as reported above; i.e., the thermal parameter (B = 0.61) of Ba was larger than that of Sb (B = 0.16) and Co/Fe (B = 0.12). The rattling of the Ba atom can reduce the mean free path of the heat-carrying phonon, resulting in lowering of the lattice thermal conductivity.

The effects of Ba filling fraction and Fe content on lattice thermal conductivity at room temperature and 800 K is shown in Fig. 7 for *p*-type $Ba_yFe_xCo_{4-x}Sb_{12}$. When x = 1.6, κ_L decreased with increasing Ba filling fraction and reached a minimum value at a Ba filling fraction of about 0.4. When y > 0.4, κ_L began to increase with increasing Ba filling fraction. When x = 1.0, lattice thermal conductivity also reached the minimum values at a certain Ba filling fraction (about 0.3). In other words, the lattice thermal conductivity was more greatly reduced when Sb-icosahedron voids are partially filled. We reported that lattice thermal conductivity reached minimum values when Ce filling fraction was 0.3 for CevFe_{1.5}Co_{2.5}Sb₁₂.^{12,20} Chen *et al.* predicted that partial filling of voids with Ce (random distribution) would provide more phonon scattering than full filling (a regular arrangement in which all the voids are filled by Ce).⁴



FIG. 5. Temperature dependence of Seebeck coefficient for *p*-type $Ba_{y}Fe_{1.6}Co_{2.4}Sb_{12}$.



FIG. 6. Temperature dependence of lattice thermal conductivity for p-type Ba_vFe_vCo_{4-v}Sb₁₂.



FIG. 7. Effect of Ba filling fraction and Fe content on lattice thermal conductivity of p-type Ba_vFe_xCo_{4-x}Sb₁₂.

Nolas *et al.* measured the low-temperature lattice thermal conductivity of $La_xCo_4(Sb,Sn)_{12}$ and reported that La scattering is most effective at x = 0.25 to 0.3.⁵ The present experimental results, results obtained for $Ce_yFe_{1.5}Co_{2.5}Sb_{12}$, and results reported by Nolas *et al.* confirmed that the random distribution of filling atoms seems to be more effective in scattering phonons than an arrangement in which all, or most, of the voids are filled.

D. The dimensionless thermoelectric figure of merit *ZT*

The dimensionless thermoelectric figure of merit (*ZT*), was calculated using $ZT = \alpha^2 \sigma T/\kappa$ from the measured electrical conductivity (σ), the Seebeck coefficient (α), and thermal conductivity (κ). The maximum *ZT* values obtained at temperature range of 300 to 800 K for *p*-type Ba_yFe_xCo_{4-x}Sb₁₂ are plotted as a function of Ba filling fraction and Fe content in Fig. 8. The maximum *ZT* values increased with Ba filling fraction and reached their maximum at some certain filling fraction. At *x* = 1.6, *ZT* showed a maximum value (0.7) at *y* = 0.4. At *x* = 1.0, *ZT* showed a maximum value at *y* = 0.3, for which a *ZT*_{max} value of 0.9 was obtained. A larger *ZT* value would be expected by optimizing Ba filling fraction at a moderately low Fe content region.

IV. SUMMARY

Single-phase barium-filled skutterudite compounds, Ba_yFe_xCo_{4-x}Sb₁₂ (x = 0 to 3.0, y = 0 to 0.7), were synthesized by a two-step solid-state reaction method. The maximum filling fraction of Ba (y_{max}) in



FIG. 8. Effect of Ba filling fraction and Fe content on maximum ZT for p-type $Ba_vFe_xCo_{4-x}Sb_{12}$ (300–800 K).

 $Ba_yFe_xCo_{4-x}Sb_{12}$ increased with increasing Fe content and was found to be rather greater than that of $Ce_yFe_xCo_{4-x}Sb_{12}$. The y_{max} varied from 0.35 to near 1.0 when Fe content changed from 0 to 4.0.

 $Ba_{v}Fe_{x}Co_{4-x}Sb_{12}$ showed *p*-type conduction at composition range of x = 0 to 3.0, y = 0 to 0.7. Carrier concentration and electrical conductivity increased with increasing Fe content, and decreased with increasing Ba filling fraction. At the same carrier concentration, electrical conductivity of *p*-type Ba_vFe_xCo_{4-x}Sb₁₂ was larger than that of *p*-type $Ce_{v}Fe_{x}Co_{4-x}Sb_{12}$. The Seebeck coefficient increased with increasing Ba filling fraction and with decreasing Fe content. Lattice thermal conductivity decreased with increasing Ba filling fraction and reached the minimum at a certain Ba filling fraction (y = 0.3 to 0.4). The greatest ZT value of 0.9 was obtained at 750 K for p-type $Ba_{0.27}Fe_{0.98}Co_{3.02}Sb_{12}$. It is expected that further investigation on the optimization of filling fraction would result in a higher ZT value at a moderately low Fe content region.

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